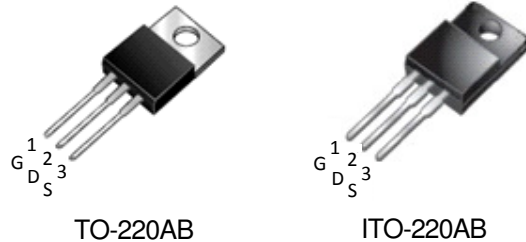


650V / 8A N-Channel Enhancement Mode MOSFET	$650V, R_{DS(ON)}=1.4\Omega@V_{GS}=10V, I_D=4.0A$
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Features

- Low ON Resistance
- Fast Switching
- Low Gate Charge & Low C_{RSS}
- Fully Characterized Avalanche Voltage and Current
- Specially Designed for AC Adapter, Battery Charger and SMPS
- In compliance with EU RoHs 2002/95/EC Directives

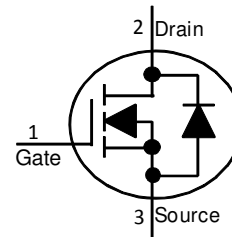


Mechanical Information

- Case: TO-220AB / ITO-220AB Molded Plastic
- Terminals : Solderable per MIL-STD-750, Method 2026

Marking & Ordering Information

TYPE	MARKING	PACKAGE	PACKING
HY8N65T	8N65T	TO-220AB	50PCS/TUBE
HY8N65FT	8N65FT	ITO-220AB	50PCS/TUBE



Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Parameter		Symbol	HY8N65T	HY8N65FT	Units
Drain-Source Voltage		V_{DS}	650		V
Gate-Source Voltage		V_{GS}	± 30		V
Continuous Drain Current	$T_c=25^\circ C$	I_D	8	8	A
Pulsed Drain Current ¹⁾		I_{DM}	32	32	A
Maximum Power Dissipation	$T_c=25^\circ C$	P_D	125	45	W
Derating Factor			1.0	0.36	
Avalanche Energy with Single Pulse $I_{AS}=8A, V_{DD}=50V, L=13mH$		E_{AS}	416		mJ
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to +150		$^\circ C$

Note : 1. Maximum DC current limited by the package

Thermal Characteristics

PARAMETER	Symbol	HY8N65T	HY8N65FT	Units
Junction-to-Case Thermal Resistance	$R_{\theta JC}$	1.0	2.78	$^\circ C/W$
Junction-to Ambient Thermal Resistance	$R_{\theta JA}$	62.5	100	$^\circ C/W$

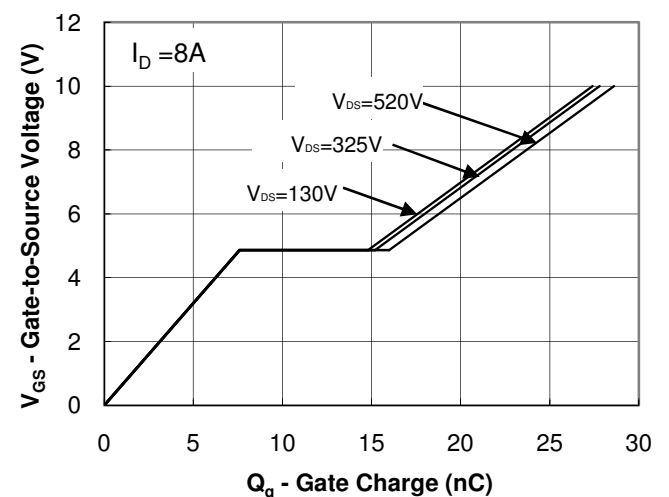
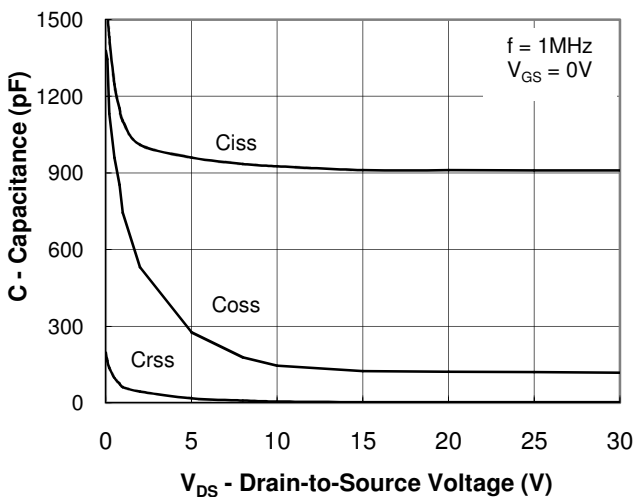
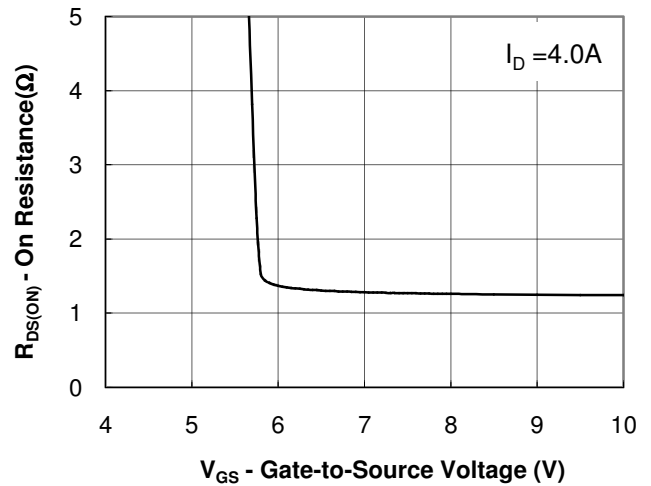
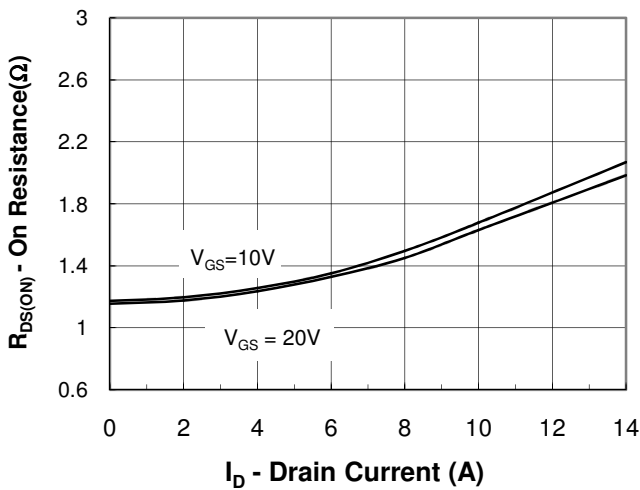
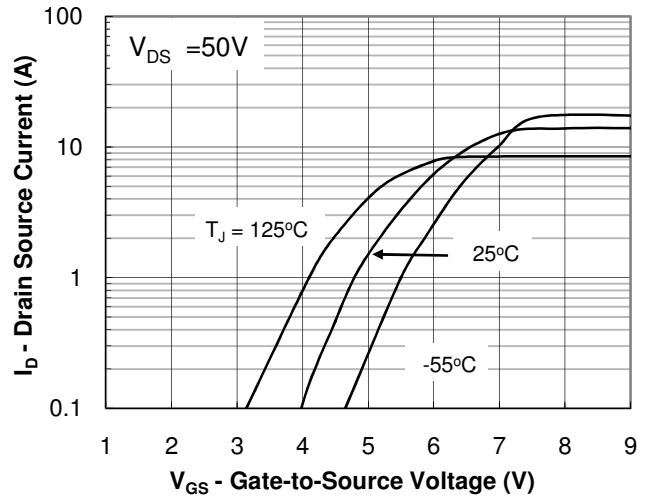
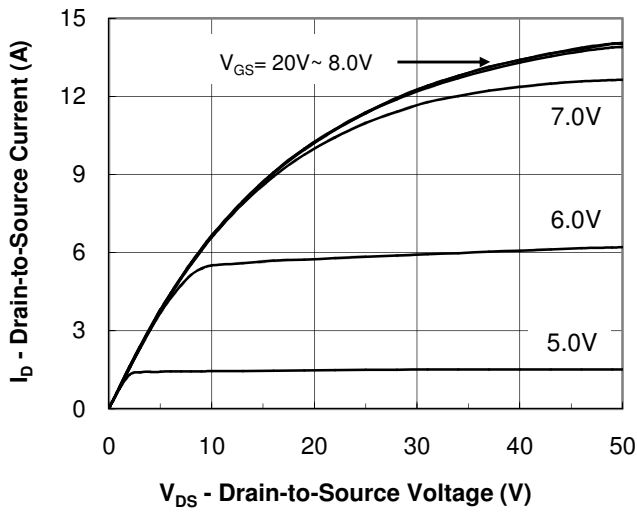
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Electrical Characteristics ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Units
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	650	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	-	4.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=4.0A$	-	1.2	1.4	Ω
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=650V, V_{GS}=0V$	-	-	10	μA
Gate Body Leakage	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0V$	-	-	± 100	nA
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=520V, I_D=8A,$ $V_{GS}=10V$	-	28.6	38	nC
Gate-Source Charge	Q_{gs}		-	7.6	-	
Gate-Drain Charge	Q_{gd}		-	8.4	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=325V, I_D=8A$ $V_{GS}=10V, R_G=25\Omega$	-	13.2	18	ns
Turn-On Rise Time	t_r		-	18.6	32	
Turn-Off Delay Time	$t_{d(off)}$		-	42.6	56	
Turn-Off Fall Time	t_f		-	16.8	22	
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V$ $f=1.0\text{MHz}$	-	900	1120	pF
Output Capacitance	C_{oss}		-	120	180	
Reverse Transfer Capacitance	C_{rss}		-	2.2	6.8	
Source-Drain Diode						
Max. Diode Forward Current	I_S	-	-	-	8	A
Max.Pulsed Source Current	I_{SM}	-	-	-	32	A
Diode Forward Voltage	V_{SD}	$I_S=8A, V_{GS}=0V$	-	-	1.3	V
Reverse Recovery Time	t_{rr}	$V_{GS}=0V, I_F=8A$ $di/dt=100A/\mu s$	-	380	-	ns
Reverse Recovery Charge	Q_{rr}		-	3.6	-	μC

NOTE : Plus Test : Pluse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

Typical Characteristics Curves ($T_C=25^\circ\text{C}$, unless otherwise noted)



Typical Characteristics Curves ($T_C=25^\circ\text{C}$, unless otherwise noted)

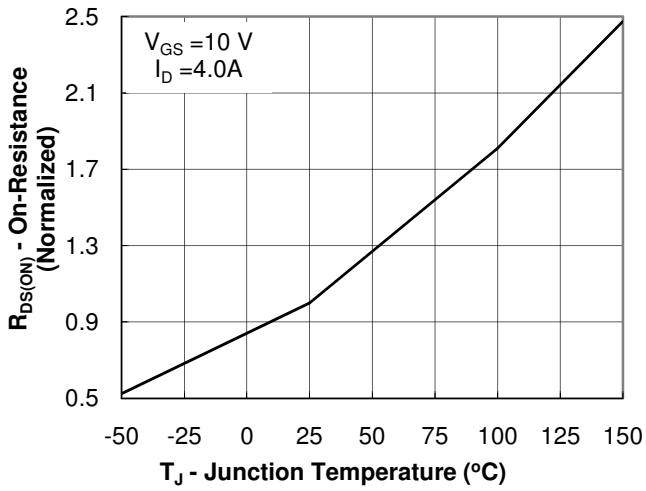


Fig.7 On-Resistance vs Junction Temperature

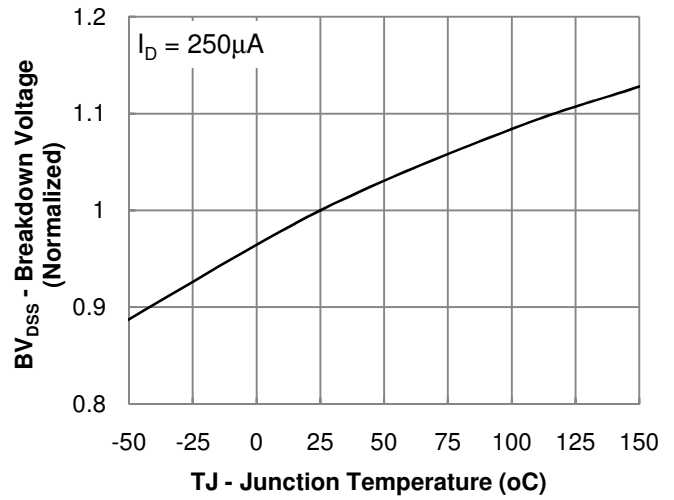


Fig.8 Breakdown Voltage vs Junction Temperature

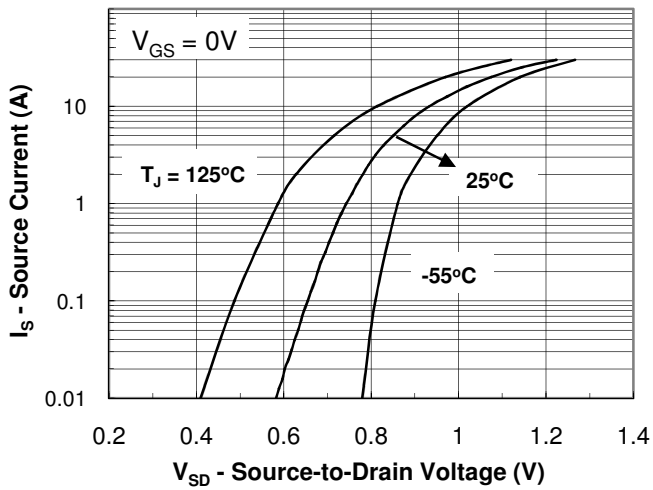


Fig.9 Body Diode Forward Voltage Characteristic